

Switching Transistor BSV52LT1G

NPN Silicon

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	12	Vdc
Collector - Base Voltage	V _{CBO}	20	Vdc
Collector Current – Continuous	Ic	100	mAdc

THERMAL CHARACTERISTICS

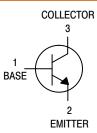
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



B2 = Device Code M = Date Code*

IVI = Date Code^{*}

■ = Pb-Free Package (Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSV52LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSV52LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = 1.0 mAdc)	V _(BR) CEO	12	_	Vdc
Collector Cutoff Current $(V_{CB} = 10 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 10 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	Ісво	- -	100 5.0	nAdc μAdc
ON CHARACTERISTICS	•	•	•	•
DC Current Gain $ \begin{aligned} &(I_C=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ &(I_C=50 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \end{aligned} $	H _{FE}	25 40 25	- 120 -	-
Collector – Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 300 μ Adc) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	V _{CE(sat)}	- - -	300 250 400	mVdc
	V _{BE(sat)}	700 -	850 1200	mVdc
SMALL-SIGNAL CHARACTERISTICS		•	•	•
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	400	_	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 1.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	4.5	pF
SWITCHING CHARACTERISTICS	·			
Storage Time $(I_C = I_{B1} = I_{B2} = 10 \text{ mAdc})$	t _s	_	13	ns
Turn–On Time ($V_{BE} = 1.5 \text{ Vdc}$, $I_{C} = 10 \text{ mAdc}$, $I_{B} = 3.0 \text{ mAdc}$)	t _{on}	-	12	ns
Turn-Off Time (I _C = 10 mAdc, I _B = 3.0 mAdc)	t _{off}	-	18	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°





DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR		NODE D CONNECTION ATHODE	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: STYLE 12: PIN 1. ANODE PIN 1. CA 2. CATHODE 2. CA 3. CATHODE-ANODE 3. AN	ATHODE PIN 1. SOURCE ATHODE 2. DRAIN	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE			STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: STYLE 24: PIN 1. ANODE PIN 1. GAT 2. ANODE 2. DR/ 3. CATHODE 3. SOU	TE PIN 1. ANODE AIN 2. CATHODE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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